

CLAIM AMENDMENTS:

1. (Currently Amended) A photoelectric converter device having a plurality of pixels formed on a substrate, comprising:

a slice check wire for checking acceptability of a cut edge of said substrate, said slice check wire being arranged outside a region where said pixels are arranged and being disposed on a first wire layer among a plurality of wire layers, closest to said substrate, on said substrate.

2. (Cancelled).

3. (Previously Presented) The photoelectric converter device according to claim 1, wherein

said wire is connected to a constant electric potential.

4. (Previously Presented) The photoelectric converter device according to claim 3, wherein

said constant electric potential is the ground potential.

5. (Previously Presented) The photoelectric converter device according to claim 1, wherein

said wire has a pad section for checking electric conductivity.

6. (Withdrawn). The semiconductor device according to claim 1,
wherein

 said peripheral wire is connected to drive wires of said functional
elements or signal wires.

7. (Withdrawn). The semiconductor device according to claim 1,
wherein

 TFT elements and photoelectric converter elements are arranged as
functional elements on said substrate and said peripheral wire is connected to bias wires of
said photoelectric converter elements.

8. (Withdrawn). The semiconductor device according to claim 6,
wherein

 TFT elements and photoelectric converter elements are arranged as
functional elements on said substrate and said peripheral wire is connected to bias wires of
said photoelectric converter elements.

9. (Previously Presented) The photoelectric converter device according
to claim 1, wherein

 said substrate is an insulator.

10. (Previously Presented) The photoelectric converter device according
to claim 1, wherein

 said pixels carry a wavelength converter thereon.

11. (Previously Presented) The photoelectric converter device according to claim 10, wherein

said wavelength converter is a fluorescent substance.

12. - 15. (Cancelled).

16. (Withdrawn). The semiconductor device according to claim 12, wherein

said peripheral wire is connected to drive wires of said functional elements or signal wires.

17. (Withdrawn). The semiconductor device according to claim 12, wherein

TFT elements and photoelectric converter elements are arranged as functional elements on said substrate and said peripheral wire is connected to bias wires of said photoelectric converter elements.

18. (Withdrawn). A semiconductor device according to claim 16, wherein

TFT elements and photoelectric converter elements are arranged as functional elements on said substrate and said peripheral wire is connected to bias wires of the photoelectric converter elements.

19. - 21. (Cancelled).

22. (Withdrawn). A semiconductor device comprising a TFT substrate having a plurality of pixels of a plurality of TFT (thin film transistors) provided on the substrate,

wherein drive wires of said TFT are connected by way of a wire resistance R_s ;

each of the pixels on said TFT substrate comprises said TFT and a photoelectric converter element, bias wires of said photoelectric converter elements and drive wires of said TFT being connected;

said TFT substrate has a slice line for cutting said TFT substrate arranged along the outer periphery thereof; and

a peripheral wire is arranged between said slice line and said TFT substrate.

23. (Withdrawn). The semiconductor device according to claim 22, said peripheral wire is used for checking the acceptability of the cutting of said substrate.

24. (Withdrawn). The semiconductor device according to claim 22, wherein

said peripheral wire is connected to a constant voltage source.

25. (Withdrawn). The semiconductor device according to claim 22, wherein

said peripheral wire is held to the ground potential.

26. (Withdrawn). The semiconductor device according to claim 22,
wherein

 said peripheral wire has a pad section for checking electric
 conductivity.

27. (Withdrawn). The semiconductor device according to claim 22,
wherein

 said peripheral wire is connected to said TFT drive wires or signal
 wires.

28. (Withdrawn). The semiconductor device according to claim 22,
wherein

 said peripheral wire is connected to bias wires of said photoelectric
 converter elements.

29. (Withdrawn). A semiconductor device according to claim 27,
wherein

 said peripheral wire is connected to the bias wires of said
 photoelectric converter elements.

30. (Withdrawn). The semiconductor device according to claim 22,
wherein

 said wire resistance R_s is expressed by $R_s > 100R_o$,

where R_o is the resistance between a TFT driver and a TFT drive terminal.

31. (Withdrawn). A radiation detection apparatus comprising:
a radiation source, and
a TFT substrate having a plurality of pixels of a plurality of TFT (thin film transistors) provided on the substrate,
wherein
each of the pixels on said TFT substrate comprises said TFT and a photoelectric converter element, bias wires of said photoelectric converter elements and drive wires of said TFT being connected;
said TFT substrate has a slice line for cutting said TFT substrate arranged along the outer periphery thereof; and
a peripheral wire is arranged between said slice line and said TFT substrate.

32. (Withdrawn). The radiation detection apparatus according to claim 31, further comprising a wavelength converter.

33. (Withdrawn). A radiation detection system having the radiation detection apparatus according to claim 31 or 32 comprising:
signal processing means for processing signals from said radiation detection apparatus;

recording means for recording signals from said signal processing means;

display means for displaying the signals from said signal processing means; and

transmission means for transmitting the signals from said signal processing means.

34. (Withdrawn). A method of manufacturing the semiconductor device according to claim 22 comprising the steps of:

cutting said substrate to predetermined dimensions along said slice lines;

examining the electric conductivity of said peripheral wire; and mounting said TFT driver and said photoelectric converter element driver after examining the electric conductivity of said peripheral wire.

35. (Withdrawn). The method according to claim 34, further comprising a step of:

connecting said peripheral wire to said TFT drive wires or the bias wires of said photoelectric converter elements.

36. (Withdrawn). The method according to claim 34, further comprising a step of:

cutting the connection of said peripheral wire and said TFT drive wires or said bias wires of said photoelectric converter elements at the connecting portion thereof after examining the electric conductivity of said peripheral wire.

37. (Withdrawn). The method according to claim 34, further comprising a step of:

bonding a plurality of substrates obtained after the cutting step.